General purpose double diode BAV23

FEATURES

- Small plastic SMD package
- Switching speed: max. 50 ns
- General application
- Continuous reverse voltage: max. 200 V
- Repetitive peak reverse voltage: max. 250 V
- Repetitive peak forward current: max. 625 mA.

APPLICATIONS

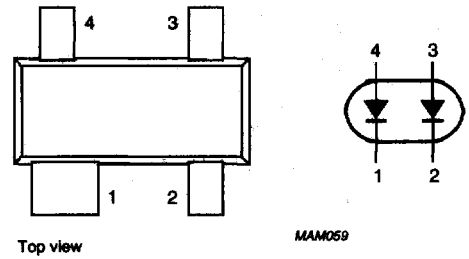
- General purpose where high breakdown voltages are required.

DESCRIPTION

The BAV23 consists of two general purpose diodes fabricated in planar technology, and encapsulated in the small plastic SMD SOT143 package. The diodes are not connected.

PINNING

PIN	DESCRIPTION
1	cathode (k1)
2	cathode (k2)
3	anode (a2)
4	anode (a1)



Marking code: L30.

Fig.1 Simplified outline (SOT143) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	250	V
V_{RRM}	repetitive peak reverse voltage	series connection		500	V
V_R	continuous reverse voltage		–	200	V
V_R	continuous reverse voltage	series connection	–	400	V
I_F	continuous forward current	single diode loaded; see Fig.2; note 1	–	225	mA
		double diode loaded; see Fig.2; note 1	–	125	mA
I_{FRM}	repetitive peak forward current		–	625	mA
I_{FSM}	non-repetitive peak forward current	square wave; T_j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	–	9	A
		t = 100 μs	–	3	A
		t = 10 ms	–	1.7	A
P_{tot}	total power dissipation	T_{amb} = 25 °C; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

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ELECTRICAL CHARACTERISTICS

T_j = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_F	forward voltage	see Fig.3			
		I_F = 100 mA	–	1.0	V
		I_F = 200 mA	–	1.25	V
V_F	forward voltage	series connection; see Fig.3			
		I_F = 100 mA	–	2.0	V
		I_F = 200 mA	–	2.5	V
I_R	reverse current	see Fig.5			
		V_R = 200 V	–	100	nA
		V_R = 200 V; T_j = 150 °C	–	100	µA
I_R	reverse current	series connection	–		
		V_R = 400 V	–	100	nA
		V_R = 400 V; T_j = 150 °C	–	100	µA
C_d	diode capacitance	f = 1 MHz; V_R = 0; see Fig.6	–	5	pF
		series connection; f = 1 MHz; V_R = 0; see Fig.6	–	2.5	pF
t_{rr}	reverse recovery time	when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA; see Fig.7	–	50	ns

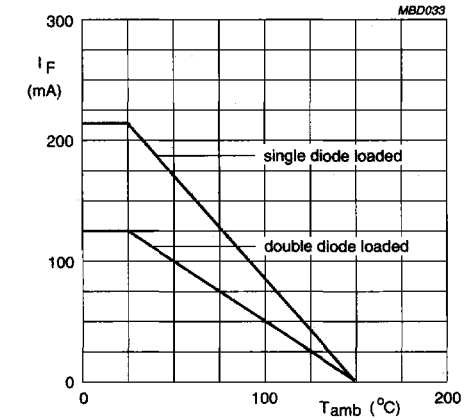
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}tp}$	thermal resistance from junction to tie-point		360	K/W
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

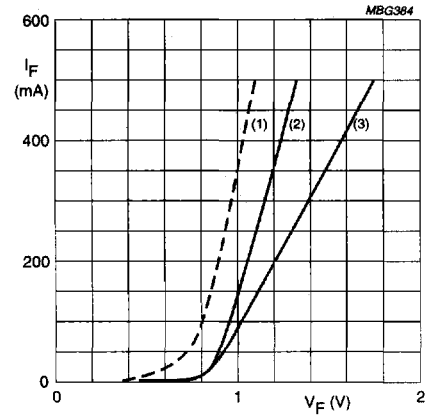
1. Device mounted on an FR4 printed-circuit board.

GRAPHICAL DATA



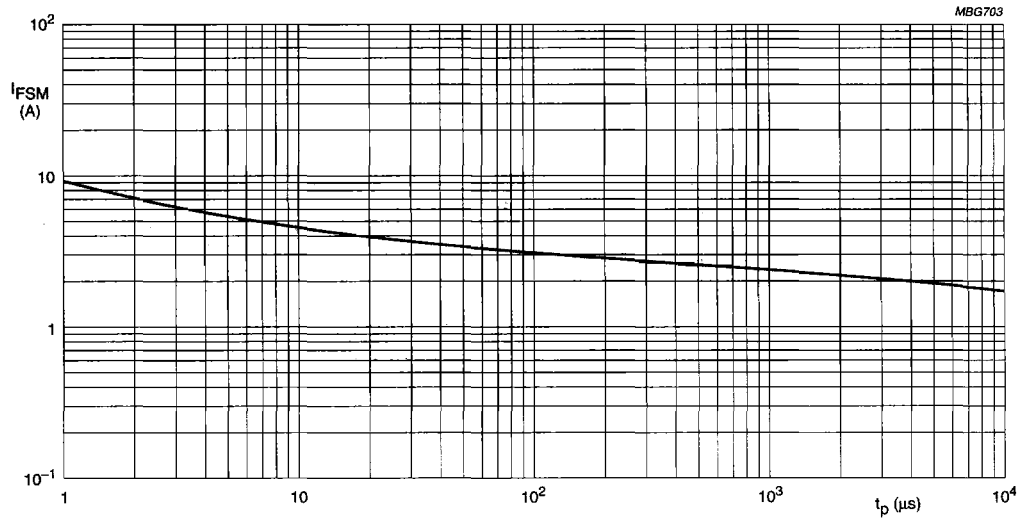
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



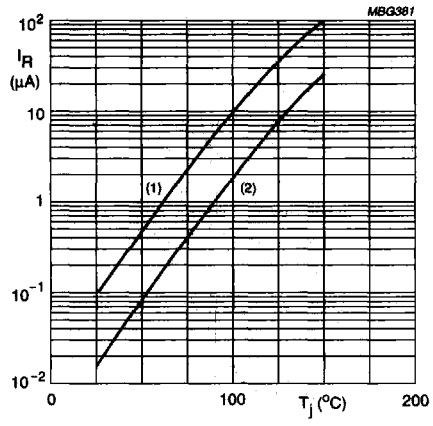
(1) T_j = 150 °C; typical values.
(2) T_j = 25 °C; typical values.
(3) T_j = 25 °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



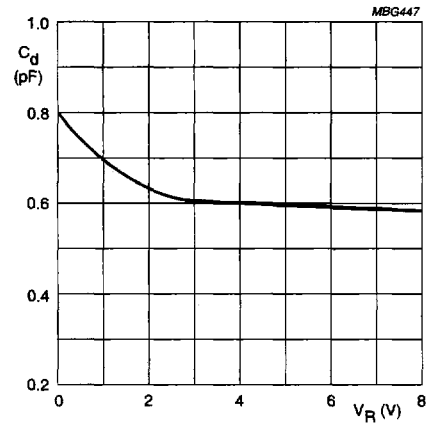
Based on square wave currents.
T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.



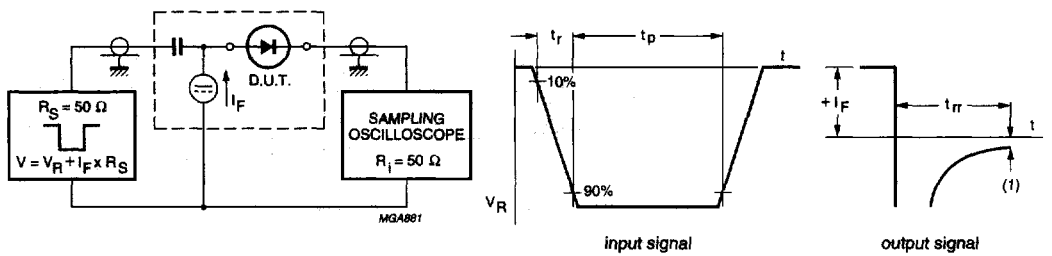
(1) V_R = 200 V; maximum values.
(2) V_R = 200 V; typical values.

Fig.5 Reverse current as a function of junction temperature.



f = 1 MHz; T_j = 25 °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.



(1) I_R = 3 mA.

Fig.7 Reverse recovery voltage test circuit and waveforms.